

SPI Serial EEPROM 1 Kbit (128 x 8), 2 Kbits (256 x 8) and 4 Kbits (512 x 8)

Features

- Serial Peripheral Interface (SPI) Compatible
- Supports SPI Modes 0 (0,0) and 3 (1,1):
 - Data sheet describes mode 0 operation
- Low-Voltage Operation:
 - 1.8V (V_{CC} = 1.8V to 5.5V)
- Industrial Temperature Range: -40°C to +85°C
- 20 MHz Clock Rate (5V)
- 8-Byte Page Mode
- Block Write Protection:
 - Protect 1/4, 1/2 or entire array
- Write-Protect (WP) Pin and Write Disable Instructions for Both Hardware and Software Data Protection
- Self-Timed Write Cycle within 5 ms Maximum
- ESD Protection > 4,000V
- High Reliability:
 - Endurance: 1,000,000 write cycles
 - Data retention: 100 years
- Green (Lead-free/Halide-free/RoHS Compliant) Package Options
- Die Sale Options: Wafer Form and Bumped Wafers

Packages

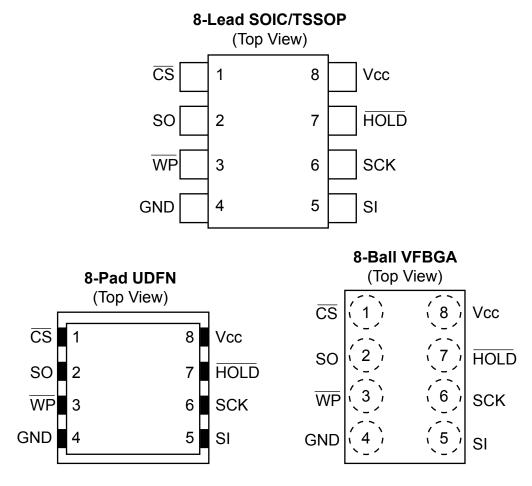
• 8-Lead SOIC, 8-Lead TSSOP, 8-Pad UDFN and 8-Ball VFBGA

Table of Contents

Fea	tures		1
Pac	kages.		1
1.	Packa	ge Types (not to scale)	4
2.		escription	
۷.	2.1.	Chip Select (CS)	
	2.1.	Serial Data Output (SO)	
	2.2.	Write-Protect (WP)	
	2.3.	Ground (GND)	
	2.5.	Serial Data Input (SI)	
	2.6.	Serial Data Clock (SCK)	
	2.7.	Suspend Serial Input (HOLD)	
	2.8.	Device Power Supply (V _{CC})	
•	-		
3.		iption	
	3.1.	SPI Bus Master Connections to Serial EEPROMs	
	3.2.	Block Diagram	8
4.	Electr	cal Characteristics	9
	4.1.	Absolute Maximum Ratings	9
	4.2.	DC and AC Operating Range	9
	4.3.	DC Characteristics	9
	4.4.	AC Characteristics	.10
	4.5.	SPI Synchronous Data Timimg	12
	4.6.	Electrical Specifications	.12
5.	Devic	e Operation	14
	5.1.	Interfacing the AT25010B/AT25020B/AT25040B on the SPI Bus	14
	5.2.	Device Opcodes	
	5.3.	Hold Function	15
	5.4.	Write Protection	16
6.	Device	e Commands and Addressing	17
	6.1.	STATUS Register Bit Definition and Function	
	6.2.	Read STATUS Register (RDSR)	
	6.3.	Write Enable (WREN) and Write Disable (WRDI)	
	6.4.	Write STATUS Register (WRSR)	
7.	Read	Sequence	
8.		Sequence	
	8.1.	Byte Write	
	8.2.	Page Write	
	8.3.	Polling Routine	23
9.	Packa	ging Information	24

9.1. Package Marking Information	24
10. Revision History	. 34
The Microchip Website	35
Product Change Notification Service	35
Customer Support	. 35
Product Identification System	36
Microchip Devices Code Protection Feature	. 36
Legal Notice	. 37
Trademarks	. 37
Quality Management System	. 38
Worldwide Sales and Service	39

1. Package Types (not to scale)



2. Pin Description

The descriptions of the pins are listed in Table 2-1.

Table 2-1. Pin Function Table

Name	8-Lead SOIC	8-Lead TSSOP	8-Pad UDFN ⁽¹⁾	8-Ball VFBGA	Function
CS	1	1	1	1	Chip Select
SO	2	2	2	2	Serial Data Output
WP ⁽²⁾	3	3	3	3	Write-Protect
GND	4	4	4	4	Ground
SI	5	5	5	5	Serial Data Input
SCK	6	6	6	6	Serial Data Clock
HOLD ⁽²⁾	7	7	7	7	Suspends Serial Input
Vcc	8	8	8	8	Device Power Supply

Note:

- 1. The exposed pad on this package can be connected to GND or left floating.
- 2. The Write-Protect (WP) and Hold (HOLD) pins should be driven high or low as appropriate.

2.1 Chip Select (CS)

The AT25010B/AT25020B/AT25040B is selected when the Chip Select (\overline{CS}) pin is low. When the device is not selected, data will not be accepted via the Serial Data Input (SI) pin, and the Serial Output (SO) pin will remain in a high-impedance state.

To ensure robust operation, the \overline{CS} pin should follow V_{CC} upon power-up. It is therefore recommended to connect \overline{CS} to V_{CC} using a pull-up resistor (less than or equal to 10 k Ω). After power-up, a low level on \overline{CS} is required prior to any sequence being initiated.

2.2 Serial Data Output (SO)

The Serial Data Output (SO) pin is used to transfer data out of the AT25010B/AT25020B/AT25040B. During a read sequence, data is shifted out on this pin after the falling edge of the Serial Data Clock (SCK).

2.3 Write-Protect (WP)

The Write-Protect (\overline{WP}) pin will allow normal read/write operations when held high. When the \overline{WP} pin is brought low, all write operations are inhibited. \overline{WP} going low while \overline{CS} is still low will interrupt a write operation. If the internal write cycle has already been initiated, \overline{WP} going low will have no effect on any write operation.

2.4 Ground (GND)

The ground reference for the Device Power Supply (V_{CC}). The Ground (GND) pin should be connected to the system ground.

2.5 Serial Data Input (SI)

The Serial Data Input (SI) pin is used to transfer data into the device. It receives instructions, addresses and data. Data is latched on the rising edge of the Serial Data Clock (SCK).

2.6 Serial Data Clock (SCK)

The Serial Data Clock (SCK) pin is used to synchronize the communication between a master and the AT25010B/ AT25020B/AT25040B. Instructions, addresses or data present on the Serial Data Input (SI) pin is latched in on the rising edge of SCK, while output on the Serial Data Output (SO) pin is clocked out on the falling edge of SCK.

2.7 Suspend Serial Input (HOLD)

The Suspend Serial Input (\overline{HOLD}) pin is used in conjunction with the Chip Select (\overline{CS}) pin to pause the AT25010B/ AT25020B/AT25040B. When the device is selected and a serial sequence is underway, \overline{HOLD} can be used to pause the serial communication with the master device without resetting the serial sequence. To pause, the \overline{HOLD} pin must be brought low while the Serial Data Clock (SCK) pin is low. To resume serial communication, the \overline{HOLD} pin is brought high while the SCK pin is low (SCK may still toggle during \overline{HOLD}). Inputs to the Serial Data Input (SI) pin will be ignored while the Serial Data Output (SO) pin will be in the high-impedance state.

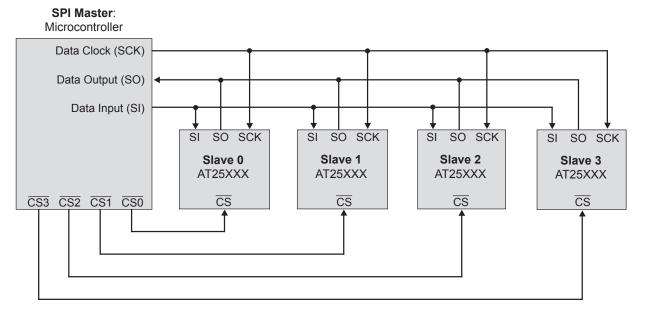
2.8 Device Power Supply (V_{CC})

The Device Power Supply (V_{CC}) pin is used to supply the source voltage to the device. Operations at invalid V_{CC} voltages may produce spurious results and should not be attempted.

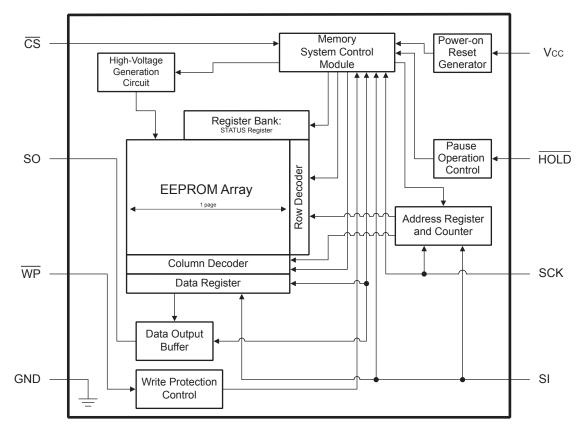
3. Description

The AT25010B/AT25020B/AT25040B provides 1,024/2,048/4,096 bits of Serial Electrically Erasable and Programmable Read-Only Memory (EEPROM) organized as 128/256/512 words of 8 bits each. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. The device is available in space-saving 8-lead SOIC, 8-lead TSSOP, 8-pad UDFN and 8-ball VFBGA packages. All packages operate from 1.8V to 5.5V.

3.1 SPI Bus Master Connections to Serial EEPROMs



3.2 Block Diagram



4. Electrical Characteristics

4.1 Absolute Maximum Ratings

Operating temperature	-40°C to +125°C
Storage temperature	-65°C to +150°C
Voltage on any pin with respect to ground	-1.0V to +7.0V
V _{cc}	6.25V
DC output current	5.0 mA
ESD protection	> 4 kV

Note: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

4.2 DC and AC Operating Range

Table 4-1. DC and AC Operating Range

AT25010B/AT25020B/AT25040B		
Operating Temperature (Case)	Industrial Temperature Range	-40°C to +85°C
V _{CC} Power Supply	Low-Voltage Grade	1.8V to 5.5V

4.3 DC Characteristics

Table 4-2. DC Characteristics⁽¹⁾

Parameter	Symbol	Minimum	Typical	Maximum	Units	Conditions
Supply Voltage	V _{CC1}	1.8		5.5	V	
Supply Voltage	V _{CC2}	2.5		5.5	V	
Supply Voltage	V _{CC3}	4.5		5.5	V	
Supply Current	I _{CC1}		8.5	10.0	mA	V _{CC} = 5.0V at 20 MHz, SO = Open, Read
Supply Current	I _{CC2}		4.5	5.0	mA	V _{CC} = 5.0V at 10 MHz, SO = Open, Read, Write
Supply Current	I _{CC3}		2.0	3.0	mA	V _{CC} = 5.0V at 1 MHz, SO = Open, Read, Write
Standby Current	I _{SB1}		0.1	0.5	μA	V_{CC} = 1.8V, \overline{CS} = V_{CC}
Standby Current	I _{SB2}		0.2	1.0	μA	V_{CC} = 2.5V, \overline{CS} = V_{CC}
Standby Current	I _{SB3}	<u> </u>	2.0	3.5	μA	V_{CC} = 5.0V, \overline{CS} = V_{CC}
Input Leakage	IIL	-3.0		3.0	μA	$V_{IN} = 0V$ to V_{CC}

Electrical Characteristics

continued								
Parameter	Symbol	Minimum	Typical	Maximum	Units	Conditi	ons	
Output Leakage	I _{OL}	-3.0	—	3.0	μA	$V_{IN} = 0V \text{ to } V_{CC},$ $T_A = 0^{\circ}C \text{ to } +70^{\circ}C$		
Input Low-Voltage	V _{IL} ⁽²⁾	-0.6	_	V _{CC} x 0.3	V			
Input High-Voltage	V _{IH} ⁽²⁾	V _{CC} x 0.7	_	V _{CC} + 0.5	V			
Output Low-Voltage	V _{OL1}	—		0.4	V	$3.6 V \leq V_{CC} \leq 5.5 V$	I _{OL} = 3.0 mA	
Output High-Voltage	V _{OH1}	V _{CC} - 0.8	_	_	V	$3.6 V \leq V_{CC} \leq 5.5 V$	I _{OH} = -1.6 mA	
Output Low-Voltage	V _{OL2}	—	_	0.2	V	1.8V ≤ V _{CC} ≤ 3.6V	I _{OL} = 0.15 mA	
Output High-Voltage	V _{OH2}	V _{CC} - 0.2		_	V	$1.8 V \leq V_{CC} \leq 3.6 V$	I _{OH} = -100 μA	

Note:

- 1. Applicable over recommended operating range from: $T_A = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = 1.8V$ to 5.5V (unless otherwise noted).
- 2. V_{IL} min and V_{IH} max are reference only and are not tested.

4.4 AC Characteristics

Table 4-3. AC Characteristics⁽¹⁾

Parameter	Symbol	Minimum	Maximum	Units	Conditions
SCK Clock Frequency	f _{SCK}	0	20	MHz	V_{CC} = 4.5V to 5.5V
		0	10	MHz	V_{CC} = 2.5V to 5.5V
		0	5	MHz	V _{CC} = 1.8V to 5.5V
Input Rise Time	t _{RI}	—	2000	ns	V_{CC} = 1.8V to 5.5V
Input Fall Time	t _{FI}	_	2000	ns	V _{CC} = 1.8V to 5.5V
SCK High Time	t _{WH}	20	—	ns	V_{CC} = 4.5V to 5.5V
		40	_	ns	V_{CC} = 2.5V to 5.5V
		80		ns	V _{CC} = 1.8V to 5.5V
SCK Low Time	t _{WL}	20	_	ns	V_{CC} = 4.5V to 5.5V
	40 —		ns	V_{CC} = 2.5V to 5.5V	
		80		ns	V _{CC} = 1.8V to 5.5V
CS High Time	t _{CS}	100	_	ns	V_{CC} = 4.5V to 5.5V
		100	_	ns	V _{CC} = 2.5V to 5.5V
		200		ns	V _{CC} = 1.8V to 5.5V

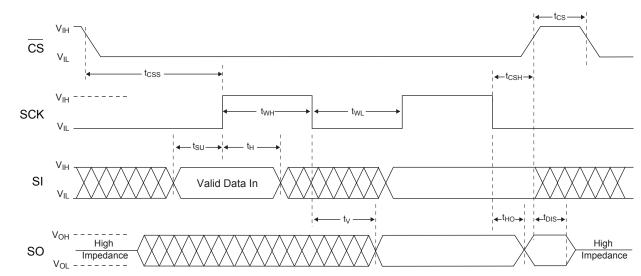
Electrical Characteristics

continued							
Parameter	Symbol	Minimum	Maximum	Units	Conditions		
CS Setup Time	t _{CSS}	100	_	ns	V_{CC} = 4.5V to 5.5V		
		100	—	ns	V_{CC} = 2.5V to 5.5V		
		200	—	ns	V_{CC} = 1.8V to 5.5V		
CS Hold Time	t _{CSH}	100	—	ns	V_{CC} = 4.5V to 5.5V		
		100	—	ns	V_{CC} = 2.5V to 5.5V		
		200	—	ns	V _{CC} = 1.8V to 5.5V		
Data In Setup Time	t _{SU}	20	—	ns	V _{CC} = 4.5V to 5.5V		
		40	—	ns	V _{CC} = 2.5V to 5.5V		
		80	_	ns	V _{CC} = 1.8V to 5.5V		
Data In Hold Time	t _H	20	_	ns	V _{CC} = 4.5V to 5.5V		
		40	_	ns	V _{CC} = 2.5V to 5.5V		
		80	_	ns	V _{CC} = 1.8V to 5.5V		
HOLD Setup Time	t _{HD}	20	_	ns	V _{CC} = 4.5V to 5.5V		
		40	_	ns	V _{CC} = 2.5V to 5.5V		
		80	_	ns	V _{CC} = 1.8V to 5.5V		
HOLD Hold Time	t _{CD}	20	_	ns	V _{CC} = 4.5V to 5.5V		
		40	_	ns	V _{CC} = 2.5V to 5.5V		
		80	_	ns	V _{CC} = 1.8V to 5.5V		
Output Valid	t _V	0	20	ns	V _{CC} = 4.5V to 5.5V		
		0	40	ns	V _{CC} = 2.5V to 5.5V		
		0	80	ns	V _{CC} = 1.8V to 5.5V		
Output Hold Time	t _{HO}	0	_	ns	V _{CC} = 4.5V to 5.5V		
		0	_	ns	V _{CC} = 2.5V to 5.5V		
		0	_	ns	V _{CC} = 1.8V to 5.5V		
HOLD to Output Low-Z	t _{LZ}	0	25	ns	V _{CC} = 4.5V to 5.5V		
		0	50	ns	V _{CC} = 2.5V to 5.5V		
		0	100	ns	V _{CC} = 1.8V to 5.5V		
HOLD to Output High-Z	t _{HZ}	_	25	ns	V _{CC} = 4.5V to 5.5V		
		_	50	ns	V _{CC} = 2.5V to 5.5V		
		_	100	ns	V _{CC} = 1.8V to 5.5V		
Output Disable Time	t _{DIS}	_	25	ns	V _{CC} = 4.5V to 5.5V		
		_	50	ns	V _{CC} = 2.5V to 5.5V		
			100	ns	V _{CC} = 1.8V to 5.5V		
Write Cycle Time	t _{WC}	_	5	ms	V _{CC} = 1.8V to 5.5V		

Electrical Characteristics

Note:

 Applicable over recommended operating range from T_A = -40°C to +85°C, V_{CC} = As Specified, C_L = 1 TTL Gate and 30 pF (unless otherwise noted).



4.5 SPI Synchronous Data Timimg

4.6 Electrical Specifications

4.6.1 Power-Up Requirements and Reset Behavior

During a power-up sequence, the V_{CC} supplied to the AT25010B/AT25020B/AT25040B should monotonically rise from GND to the minimum V_{CC} level, as specified in Table 4-1, with a slew rate no faster than 0.1 V/ μ s.

4.6.1.1 Device Reset

To prevent inadvertent write operations or any other spurious events from occurring during a power-up sequence, the AT25010B/AT25020B/AT25040B includes a Power-on Reset (POR) circuit. Upon power-up, the device will not respond to any instructions until the V_{CC} level crosses the internal voltage threshold (V_{POR}) that brings the device out of Reset and into Standby mode.

The system designer must ensure the instructions are not sent to the device until the V_{CC} supply has reached a stable value greater than or equal to the minimum V_{CC} level. Additionally, once the V_{CC} is greater than or equal to the minimum V_{CC} level, the bus master must wait at least t_{PUP} before sending the first instruction to the device. See Table 4-4 for the values associated with these power-up parameters.

Symbol	Parameter	Min.	Max.	Units
t _{PUP}	Time required after $V_{\mbox{\scriptsize CC}}$ is stable before the device can accept instructions	100	_	μs
V _{POR}	Power-on Reset Threshold Voltage	_	1.5	V
t _{POFF}	Minimum time at V _{CC} = 0V between power cycles	500	_	ms

Note:

1. These parameters are characterized but they are not 100% tested in production.

If an event occurs in the system where the V_{CC} level supplied to the AT25010B/AT25020B/AT25040B drops below the maximum V_{POR} level specified, it is recommended that a full-power cycle sequence be performed by first driving

Electrical Characteristics

the V_{CC} pin to GND in less than 1 ms, waiting at least the minimum t_{POFF} time and then performing a new power-up sequence in compliance with the requirements defined in this section.

4.6.2 Pin Capacitance

Table 4-5. Pin Capacitance^(1,2)

Symbol	Test Condition	Max.	Units	Conditions
C _{OUT}	Output Capacitance (SO)	8	pF	V _{OUT} = 0V
C _{IN}	Input Capacitance (CS, SCK, SI, WP, HOLD)	6	pF	V _{IN} = 0V

Note:

- 1. This parameter is characterized but is not 100% tested in production.
- 2. Applicable over recommended operating range from: $T_A = 25^{\circ}C$, $f_{SCK} = 1.0$ MHz, $V_{CC} = 5.0V$ (unless otherwise noted).

4.6.3 EEPROM Cell Performance Characteristics

Table 4-6. EEPROM Cell Performance Characteristics

Operation	Test Condition	Min.	Max.	Units
Write Endurance ⁽¹⁾	$T_A = 25^{\circ}C$, $V_{CC} = 5.0V$, Page Write mode	1,000,000	_	Write Cycles
Data Retention ⁽¹⁾	T _A = 55°C	100	—	Years

Note:

1. Performance is determined through characterization and the qualification process.

4.6.4 Software Reset

The SPI interface of the AT25010B/AT25020B/AT25040B can be reset by toggling the \overline{CS} input. If the \overline{CS} line is already in the Active state, it must complete a transition from the Inactive state ($\geq V_{IH}$) to the Active state ($\leq V_{IL}$) and then back to the Inactive state ($\geq V_{IH}$) without sending clocks on the SCK line. Upon completion of this sequence, the device will be ready to receive a new opcode on the SI line.

4.6.5 Device Default State at Power-Up

The AT25010B/AT25020B/AT25040B default state upon power-up consists of:

- Standby Power mode
- A high-to-low-level transition on CS is required to enter Active state
- Write Enable Latch (WEL) bit in the STATUS register = 0
- Ready/Busy bit in the STATUS register = 0, indicating the device is ready to accept a new command
- Device is not selected
- Not in Hold condition
- BP1 and BP0 bits in the STATUS register are unchanged from their previous state due to the fact that they are nonvolatile values

4.6.6 Device Default Condition

The AT25010B/AT25020B/AT25040B is shipped from Microchip to the customer with the EEPROM array set to an all FFh data pattern (logic '1' state). The Block Write-Protect bits in the STATUS register are set to logic '0'.

5. Device Operation

The AT25010B/AT25020B/AT25040B is controlled by a set of instructions that are sent from a host controller, commonly referred to as the SPI Master. The SPI Master communicates with the AT25010B/AT25020B/AT25040B via the SPI bus which is comprised of four signal lines: Chip Select (\overline{CS}), Serial Data Clock (SCK), Serial Data Input (SI) and Serial Data Output (SO).

The SPI protocol defines a total of four modes of operation (Mode 0, 1, 2 or 3) with each mode differing in respect to the SCK polarity and phase and how the polarity and phase control the flow of data on the SPI bus. The AT25010B/ AT25020B/AT25040B supports the two most common modes, SPI Modes 0 and 3. With SPI Modes 0 and 3, data is always latched in on the rising edge of SCK and always output on the falling edge of SCK. The only difference between SPI Modes 0 and 3 is the polarity of the SCK signal when in the inactive state (when the SPI Master is in Standby mode and not transferring any data). SPI Mode 0 is defined as a low SCK while \overline{CS} is not asserted (at V_{CC}) and SPI Mode 3 has SCK high in the inactive state. The SCK Idle state must match when the \overline{CS} is deasserted both before and after the communication sequence in SPI Mode 0 and 3. The figures in this document depict Mode 0 with a solid line on SCK while \overline{CS} is inactive and Mode 3 with a dotted line.

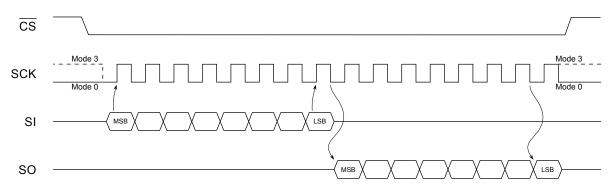


Figure 5-1. SPI Mode 0 and Mode 3

5.1 Interfacing the AT25010B/AT25020B/AT25040B on the SPI Bus

Communication to and from the AT25010B/AT25020B/AT25040B must be initiated by the SPI Master device, such as a microcontroller. The SPI Master device must generate the serial clock for the AT25010B/AT25020B/AT25040B on the Serial Data Clock (SCK) pin. The AT25010B/AT25020B/AT25040B always operates as a slave due to the fact that the SCK is always an input.

5.1.1 Selecting the Device

The AT25010B/AT25020B/AT25040B is selected when the Chip Select (\overline{CS}) pin is low. When the device is not selected, data will not be accepted via the Serial Data Input (SI) pin, and the Serial Data Output (SO) pin will remain in a high-impedance state.

5.1.2 Sending Data to the Device

The AT25010B/AT25020B/AT25040B uses the SI pin to receive information. All instructions, addresses and data input bytes are clocked into the device with the Most Significant bit (MSb) first. The SI pin samples on the first rising edge of the SCK line after the \overline{CS} has been asserted.

5.1.3 Receiving Data from the Device

Data output from the device is transmitted on the SO pin, with the MSb output first. The SO data is latched on the first falling edge of SCK after the instruction has been clocked into the device, such as the Read from Memory Array (READ) and Read STATUS Register (RDSR) instructions. See Read Sequence for more details.

5.2 Device Opcodes

5.2.1 Serial Opcode

After the device is selected by driving \overline{CS} low, the first byte will be received on the SI pin. This byte contains the opcode that defines the operation to be performed. Refer to Table 6-1 for a list of all opcodes that the AT25010B/AT25020B/AT25040B will respond to.

5.2.2 Invalid Opcode

If an invalid opcode is received, no data will be shifted into AT25010B/AT25020B/AT25040B and the SO pin will remain in a high-impedance state until the falling edge of \overline{CS} is detected again. This will reinitialize the serial communication.

5.3 Hold Function

The Suspend Serial Input (HOLD) pin is used to pause the serial communication with the device without having to stop or reset the clock sequence. The Hold mode, however, does not have an effect on the internal write cycle. Therefore, if a write cycle is in progress, asserting the HOLD pin will not pause the operation and the write cycle will continue to completion.

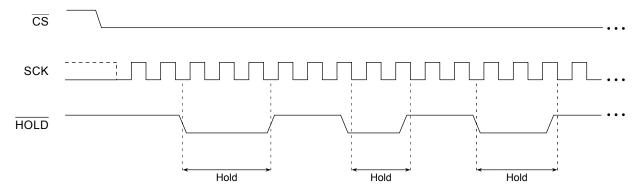
The Hold mode can only be entered while the \overline{CS} pin is asserted. The Hold mode is activated by asserting the \overline{HOLD} pin during the SCK low pulse. If the \overline{HOLD} pin is asserted during the SCK high pulse, then the Hold mode will not be started until the beginning of the next SCK low pulse. The device will remain in the Hold mode as long as the \overline{HOLD} pin and \overline{CS} pin are asserted.

While in Hold mode, the SO pin will be in a high-impedance state. In addition, both the SI pin and the SCK pin will be ignored. The Write-Protect (\overline{WP}) pin, however, can still be asserted or deasserted while in the Hold mode.

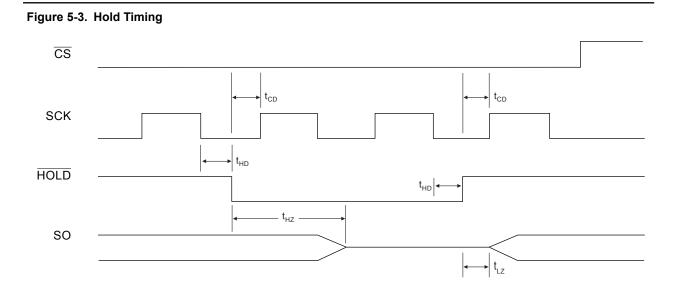
To end the Hold mode and resume serial communication, the HOLD pin must be deasserted during the SCK low pulse. If the HOLD pin is deasserted during the SCK high pulse, then the Hold mode will not end until the beginning of the next SCK low pulse.

If the \overline{CS} pin is deasserted while the \overline{HOLD} pin is still asserted, then any operation that may have been started will be aborted and the device will reset the WEL bit in the STATUS register back to the logic '0' state.

Figure 5-2. Hold Mode



Device Operation



5.4 Write Protection

The Write-Protect (\overline{WP}) pin will allow normal read and write operations when held high. When the \overline{WP} pin is brought low, all write operations are inhibited. The \overline{WP} pin going low while \overline{CS} is still low will interrupt a write operation. If the internal write cycle has already been initiated, \overline{WP} going low will have no effect on any write operation.

Device Commands and Addressing

6. Device Commands and Addressing

The AT25010B/AT25020B/AT25040B is designed to interface directly with the synchronous Serial Peripheral Interface (SPI). The AT25010B/AT25020B/AT25040B utilizes an 8-bit instruction register. The list of instructions and their operation codes are contained in Table 6-1. All instructions, addresses and data are transferred with the MSb first and start with a high-to-low \overline{CS} transition.

Instruction Name	Instruction Format	Operates On	Operation Description
WREN	0000 X110	STATUS Register	Set Write Enable Latch (WEL)
WRDI	0000 X100	STATUS Register	Reset Write Enable Latch (WEL)
RDSR	0000 X101	STATUS Register	Read STATUS Register
WRSR	0000 X001	STATUS Register	Write STATUS Register
READ	0000 A011	Memory Array	Read from Memory Array
WRITE	0000 A010	Memory Array	Write to Memory Array

Table 6-1. Instruction Set for the AT25010B/AT25020B/AT25040B

Note:

1. "A" represents the MSb address bit (A₈) for the AT25040B and a "don't care" bit for the AT25010B and AT25020B.

6.1 STATUS Register Bit Definition and Function

The AT25010B/AT25020B/AT25040B includes an 8-bit STATUS register. The STATUS register bits modulate various features of the device as shown in Table 6-2 and Table 6-3. These bits can be changed by specific instructions that are detailed in the following sections.

Table 6-2. STATUS Register Format

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Х	Х	Х	Х	BP1	BP0	WEL	RDY/BSY

Table 6-3. STATUS Register Bit Definition

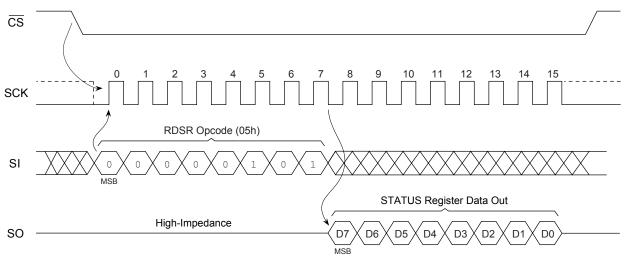
Bit		Name	Туре	Description			
7:4	RFU	Reserved for Future Use	R	0	Reads as zeros when the device is not in a write cycle		
				1	Reads as ones when the device is in a write cycle		
3:2	BP1	Block Write Protection		00	No array write protection (Factory Default)		
	BP0			01	Quarter array write protection (see Table 6-4)		
				10	Half array write protection (see Table 6-4)		
				11	Entire array write protection (see Table 6-4)		
1	WEL	L Write Enable Latch		Write Enable Latch		0	Device is not write enabled (Power-up Default)
				1	Device is write enabled		
0	RDY/BSY	Ready/Busy Status	R	0	Device is ready for a new sequence		
				1	Device is busy with an internal operation		

Device Commands and Addressing

6.2 Read STATUS Register (RDSR)

The Read STATUS Register (RDSR) instruction provides access to the STATUS register. The ready/busy and write enable status of the device can be determined by the RDSR instruction. Similarly, the Block Write-Protect (BP1, BP0) bits indicate the extent of memory array protection employed. The STATUS register is read by asserting the \overline{CS} pin, followed by sending in a 05h opcode on the SI pin. Upon completion of the opcode, the device will return the 8-bit STATUS register value on the SO pin.

Figure 6-1. RDSR Waveform



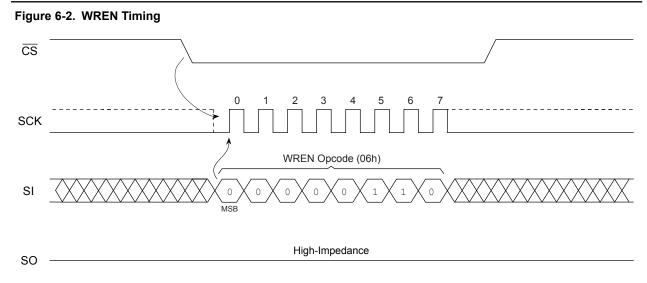
6.3 Write Enable (WREN) and Write Disable (WRDI)

Enabling and disabling writing to the STATUS register and EEPROM array is accomplished through the Write Enable (WREN) instruction and the Write Disable (WRDI) instruction. These functions change the status of the WEL bit in the STATUS register.

6.3.1 Write Enable Instruction (WREN)

The Write Enable Latch (WEL) bit of the STATUS register must be set to a logic '1' prior to each Write STATUS Register (WRSR) and Write to Memory Array (WRITE) instructions. This is accomplished by sending a WREN (06h) instruction to the AT25010B/AT25020B/AT25040B. First, the \overline{CS} pin is driven low to select the device and then a WREN instruction is clocked in on the SI pin. Then the \overline{CS} pin can be driven high and the WEL bit will be updated in the STATUS register to a logic '1'. The device will power-up in the Write Disable state (WEL = 0). The \overline{WP} pin must be held high during a WREN instruction.

Device Commands and Addressing



6.3.2 Write Disable Instruction (WRDI)

To protect the device against inadvertent writes, the Write Disable (WRDI) instruction (opcode 04h) disables all programming modes by setting the WEL bit to a logic '0'. The WRDI instruction is independent of the status of the WP pin.

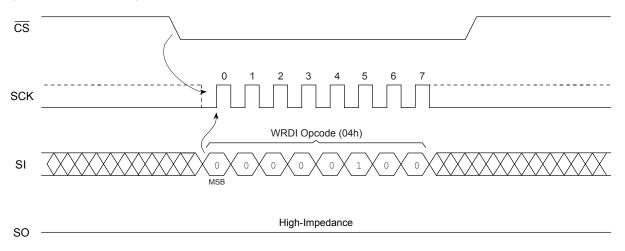


Figure 6-3. WRDI Timing

6.4 Write STATUS Register (WRSR)

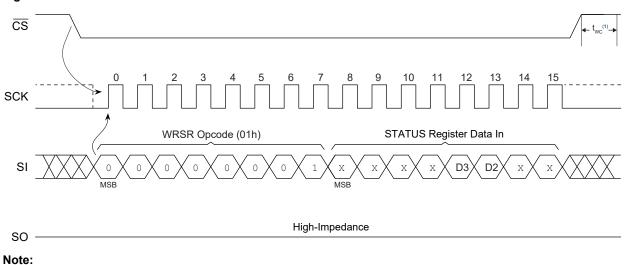
The Write STATUS Register (WRSR) instruction enables the SPI Master to change selected bits of the STATUS register. Before a WRSR instruction can be initiated, a WREN instruction must be executed to set the WEL bit to logic '1'. Upon completion of a WREN instruction, a WRSR instruction can be executed.

Note: The WRSR instruction has no effect on bit 7, bit 6, bit 5, bit 4, bit 1 and bit 0 of the STATUS register. Only bit 3 and bit 2 can be changed via the WRSR instruction. These modifiable bits are the Block Protect (BP1, BP0) bits. These bits are nonvolatile bits that have the same properties and functions as regular EEPROM cells. Their values are retained while power is removed from the device.

The AT25010B/AT25020B/AT25040B will not respond to commands other than a RDSR after a WRSR instruction until the self-timed internal write cycle has completed. When the write cycle is completed, the WEL bit in the STATUS register is reset to logic '0'.

Device Commands and Addressing

Figure 6-4. WRSR Waveform



1. This instruction initiates a self-timed internal write cycle (t_{WC}) on the rising edge of \overline{CS} after a valid sequence.

6.4.1 Block Write-Protect Function

The WRSR instruction allows the user to select one of four possible combinations as to how the memory array will be inhibited from writing through changing the Block Write-Protect bits (BP1, BP0). The four levels of array protection are:

- None of the memory array is protected.
- Upper quarter (1/4) address range is write-protected meaning the highest order address bits are read-only.
- Upper half (1/2) address range is write-protected meaning the highest order address bits are read-only.
- All of the memory array is write-protected meaning all address bits are read-only.

The Block Write Protection levels and corresponding STATUS register control bits are shown in Table 6-4.

Level	STATUS Register Bits		Write-Protected/Read-Only Address Range				
	BP1	BP0	AT25010B	AT25020B	AT25040B		
0	0	0	None	None	None		
1(1/4)	0	1	60h-7Fh	C0h-FFh	180h-1FFh		
2(1/2)	1	0	40h-7Fh	80h-FFh	100h-1FFh		
3(All)	1	1	00h-7Fh	00h-FFh	000h-1FFh		

Table 6-4. Block Write-Protect Bits

7. Read Sequence

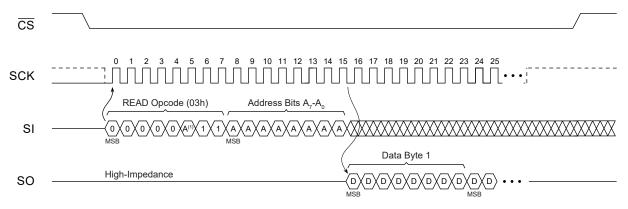
Reading the AT25010B/AT25020B/AT25040B via the SO pin requires the following sequence. After the \overline{CS} line is pulled low to select a device, the READ (03h) instruction (including A₈ for the AT25040B) is transmitted via the SI line followed by the 8-bit address to be read (A₇ - A₀). Refer to Table 7-1 for the address bits for AT25010B/AT25020B/AT25040B.

Table 7-1. AT25010B/AT25020B/AT25040B Address Bits

Address	AT25010B	AT25020B	AT25040B
A _N	A ₆ -A ₀	A ₇ -A ₀	A ₈ -A ₀
Don't Care Bits	A ₇	None	None

Upon completion of the 8-bit address, any data on the SI line will be ignored. The data (D_7-D_0) at the specified address is then shifted out onto the SO line. If only one byte is to be read, the \overline{CS} line should be driven high after the data comes out. The read sequence can be continued since the byte address is automatically incremented and data will continue to be shifted out. When the highest-order address bit is reached, the address counter will rollover to the lowest-order address bit allowing the entire memory to be read in one continuous read cycle regardless of the starting address.





Note:

1. "A" represents the MSb address bit (A₈) for the AT25040B and a "don't care" bit for the AT25010B and AT25020B.

8. Write Sequence

In order to program the AT25010B/AT25020B/AT25040B, two separate instructions must be executed. First, the device *must be write enabled* via the Write Enable (WREN) instruction. Then, one of the two possible write sequences described in this section may be executed.

Note: If the \overline{WP} pin is brought low or the device is not Write Enabled (WREN), the device will ignore the WRITE instruction and will return to the standby state when \overline{CS} is brought high. A new \overline{CS} assertion is required to re-initiate communication.

The address of the memory location(s) to be programmed must be outside the protected address field location selected by the block write protection level. During an internal write cycle, all commands will be ignored except the RDSR instruction. Refer to Table 8-1 for the address bits for AT25010B/AT25020B/AT25040B.

Table 0-1. AT250	Table 0-1. AT25010D/AT25020D/AT25040D AUULESS DILS						

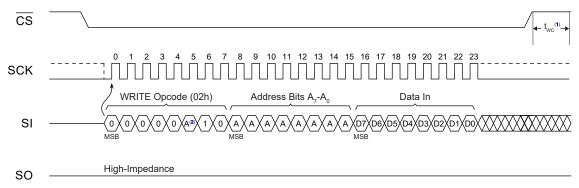
Table 0.4 AT25040D/AT25020D/AT25040D Address Dite

Address	AT25010B	AT25020B	AT25040B
A _N	A ₆ -A ₀	A ₇ -A ₀	A ₈ -A ₀
Don't Care Bits	A ₇	None	None

8.1 Byte Write

A byte write requires the following sequence and is depicted in Figure 8-1. After the \overline{CS} line is pulled low to select the device, the WRITE (02h) instruction (including A₈ for the AT25040B) is transmitted via the SI line followed by the 8-bit address and the data (D7-D0) to be programmed. Programming will start after the \overline{CS} pin is brought high. The low-to-high transition of the \overline{CS} pin must occur during the SCK low time (Mode 0) and SCK high time (Mode 3) immediately after clocking in the D0 (LSB) data bit. The AT25010B/AT25020B/AT25040B is automatically returned to the Write Disable state (STATUS register bit WEL = 0) at the completion of a write cycle.

Figure 8-1. Byte Write



Note:

- 1. This instruction initiates a self-timed internal write cycle (t_{WC}) on the rising edge of \overline{CS} after a valid sequence.
- 2. "A" represents the MSb address bit (A₈) for the AT25040B and a "don't care" bit for the AT25010B and AT25020B.

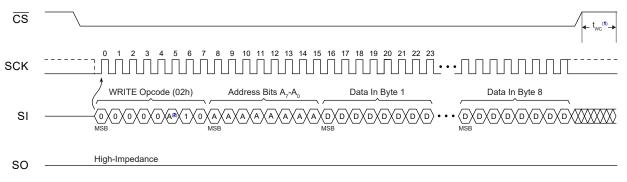
8.2 Page Write

A page write sequence allows up to 8 bytes to be written in the same write cycle, provided that all bytes are in the same row of the memory array. Partial page writes of less than 8 bytes are allowed. After each byte of data is received, the three lowest order address bits are internally incremented following the receipt of each data byte. The higher order address bits are not incremented and retain the memory array page location. If more bytes of data are transmitted than will fit to the end of that memory row, the address counter will rollover to the beginning of the same row. Nevertheless, creating a rollover event should be avoided as previously loaded data in the page could become

Write Sequence

unintentionally altered. The AT25010B/AT25020B/AT25040B is automatically returned to the Write Disable state (WEL = 0) at the completion of a write cycle.

Figure 8-2. Page Write



Note:

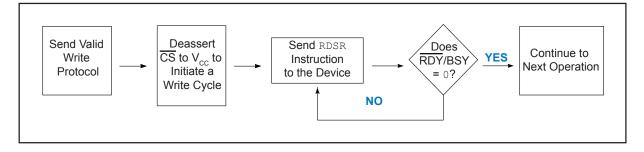
- 1. This instruction initiates a self-timed internal write cycle (t_{WC}) on the rising edge of \overline{CS} after a valid sequence.
- "A" represents the MSb address bit (A₈) for the AT25040B and a "don't care" bit for the AT25010B and AT25020B.

8.3 Polling Routine

A polling routine can be implemented to optimize time-sensitive applications that would not prefer to wait the fixed maximum write cycle time (t_{WC}). This method allows the application to know immediately when the write cycle has completed to start a subsequent operation.

Once the internally-timed write cycle has started, a polling routine can be initiated. This involves repeatedly sending Read STATUS Register (RDSR) instruction to determine if the device has completed its self-timed internal write cycle. If the \overline{RDY}/BSY bit (bit 0 of STATUS register) = 1, the write cycle is still in progress. If bit 0 = 0, the write cycle has ended. If the \overline{RDY}/BSY bit = 1, repeated RDSR commands can be executed until the \overline{RDY}/BSY bit = 0, signaling that the device is ready to execute a new instruction. Only the Read STATUS Register (RDSR) instruction is enabled during the write cycle.

Figure 8-3. Polling Flowchart

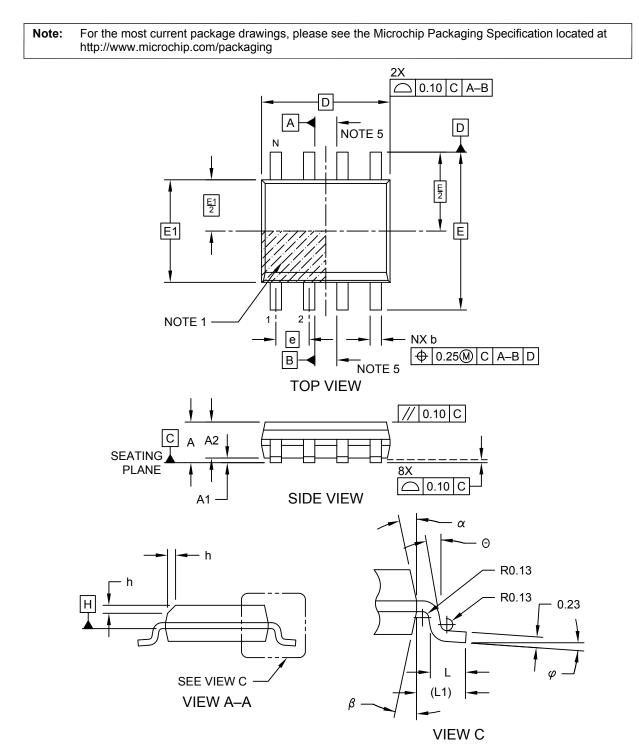


9. Packaging Information

9.1 Package Marking Information

		8-lead	SOIC		8-lead TSSOP		
			ATMLHY ###% YYWWNN	CO	ATHYWW ###%CO YYWWNNN		
		8-pad	UDFN		8-ball VFBGA		
		2.0 x 3.0	mm Body		1.5 x 2.0 mm Body		
			### H% NNN ●		###U ₩NNN ●		
			signates pin 1 ge drawings are r	not to scale			
AT25010B AT25020B	ımber Trunca	tion	Trunca	ation Code ## ation Code ##	#: 52B		
AT25010B AT25020B AT25040B		tion	Trunca		#: 52B		
AT25010B AT25020B AT25040B Date Code			Trunca	ation Code ## ation Code ##	#: 52B #: 54B	Voltage	
AT25010B AT25020B AT25040B Date Code YY = Year 16: 2016 17: 2017 18: 2018	s 20: 2020 21: 2021 22: 2022	Y = Year 6: 2016 0: 7: 2017 1: 8: 2018 2:	Trunca Trunca : 2020 : 2021 : 2022	ation Code ## ation Code ## WW = Wc 02: Week 04: Week 	#: 52B #: 54B ork Week of Assembly 2 4	% =	s - Minimum Voltage 1.8V min
AT25010B AT25020B AT25040B Date Code YY = Year 16: 2016 17: 2017 18: 2018 19: 2019	s 20: 2020 21: 2021 22: 2022 23: 2023	Y = Year 6: 2016 0: 7: 2017 1: 8: 2018 2:	Trunca Trunca : 2020 : 2021	ation Code ## ation Code ## WW = Wo 02: Week 04: Week 52: Week	#: 52B #: 54B ork Week of Assembly 2 4	——————————————————————————————————————	Minimum Voltage 1.8V min
AT25010B AT25020B AT25040B Date Code: YY = Year 16: 2016 17: 2017 18: 2018 19: 2019 Country of	s 20: 2020 21: 2021 22: 2022 23: 2023	Y = Year 6: 2016 0: 7: 2017 1: 8: 2018 2:	Trunc: Trunc: 2020 2021 2022 2023 Device	ation Code ## ation Code ## WW = Wo 02: Week 04: Week 52: Week	#: 52B #: 54B ork Week of Assembly 2 4 52	% = L: Atmel T AT:	Minimum Voltage 1.8V min runcation Atmel Atmel

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm (.150 In.) Body [SOIC]

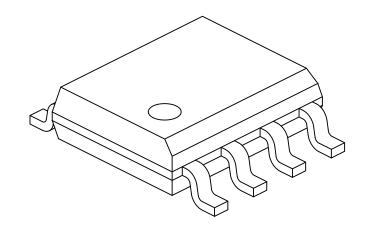


Microchip Technology Drawing No. C04-057-SN Rev E Sheet 1 of 2

Packaging Information

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm (.150 In.) Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS				
Dimensio	on Limits	MIN	NOM	MAX	
Number of Pins	Ν		8		
Pitch	е	1.27 BSC			
Overall Height	Α	-	-	1.75	
Molded Package Thickness	A2	1.25	-	-	
Standoff §	A1	0.10	-	0.25	
Overall Width	E	6.00 BSC			
Molded Package Width	E1	3.90 BSC			
Overall Length	D	4.90 BSC			
Chamfer (Optional)	h	0.25	-	0.50	
Foot Length	L	0.40	-	1.27	
Footprint	L1		1.04 REF		
Foot Angle	φ	0°	-	8°	
Lead Thickness	С	0.17	-	0.25	
Lead Width	b	0.31	-	0.51	
Mold Draft Angle Top	α	5°	-	15°	
Mold Draft Angle Bottom	β	5°	-	15°	

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. § Significant Characteristic

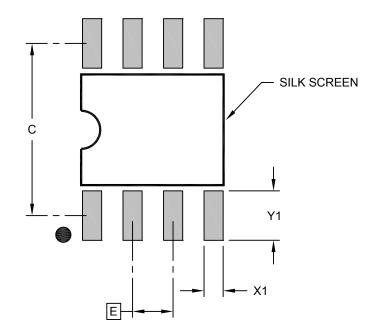
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M
 - BSC: Basic Dimension. Theoretically exact value shown without tolerances.
 - REF: Reference Dimension, usually without tolerance, for information purposes only.
- 5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-057-SN Rev E Sheet 2 of 2

Packaging Information

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	MILLIMETERS			
Dimension	MIN	NOM	MAX	
Contact Pitch	E		1.27 BSC	
Contact Pad Spacing	С		5.40	
Contact Pad Width (X8)	X1			0.60
Contact Pad Length (X8)	Y1			1.55

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

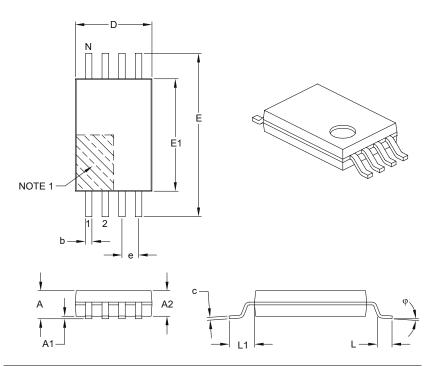
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-2057-SN Rev E

Packaging Information

8-Lead Plastic Thin Shrink Small Outline (ST) – 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	MILLIMETERS			
	Dimension Limits	MIN	NOM	MAX	
Number of Pins	N		8		
Pitch	е	0.65 BSC			
Overall Height	A	-	-	1.20	
Molded Package Thickness	A2	0.80	1.00	1.05	
Standoff	A1	0.05	-	0.15	
Overall Width	E		6.40 BSC		
Molded Package Width	E1	4.30	4.40	4.50	
Molded Package Length	D	2.90	3.00	3.10	
Foot Length	L	0.45	0.60	0.75	
Footprint	L1		1.00 REF		
Foot Angle	φ	0°	-	8°	
Lead Thickness	С	0.09	-	0.20	
Lead Width	b	0.19	-	0.30	

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15 mm per side.

3. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

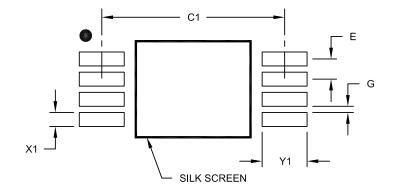
REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-086B

Packaging Information

8-Lead Plastic Thin Shrink Small Outline (ST) - 4.4 mm Body [TSSOP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	Units	N	/ILLIMETER:	S
Dimension	Limits	MIN	NOM	MAX
Contact Pitch	E		0.65 BSC	
Contact Pad Spacing	C1		5.90	
Contact Pad Width (X8)	X1			0.45
Contact Pad Length (X8)	Y1			1.45
Distance Between Pads	G	0.20		

Notes:

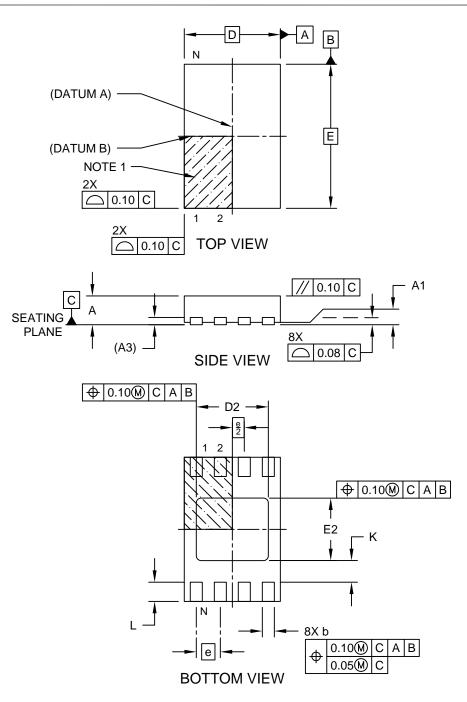
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2086A

8-Lead Ultra Thin Plastic Dual Flat, No Lead Package (Q4B) - 2x3 mm Body [UDFN] Atmel Legacy YNZ Package

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

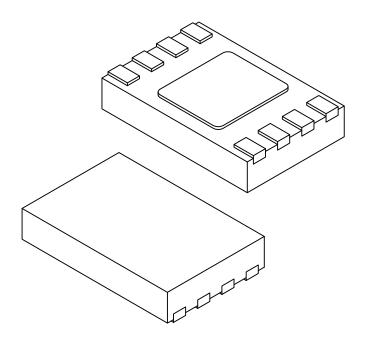


Microchip Technology Drawing C04-21355-Q4B Rev A Sheet 1 of 2

Packaging Information

8-Lead Ultra Thin Plastic Dual Flat, No Lead Package (Q4B) - 2x3 mm Body [UDFN] Atmel Legacy YNZ Package

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	Ν	IILLIMETER	S
Dimensior	n Limits	MIN	NOM	MAX
Number of Terminals	N		8	-
Pitch	е	0.50 BSC		
Overall Height	Α	0.50	0.55	0.60
Standoff	A1	0.00	0.02	0.05
Terminal Thickness	A3		0.152 REF	
Overall Length	D		2.00 BSC	
Exposed Pad Length	D2	1.40	1.50	1.60
Overall Width	E	3.00 BSC		
Exposed Pad Width	E2	1.20	1.30	1.40
Terminal Width	b	0.18	0.25	0.30
Terminal Length	L	0.35	0.40	0.45
Terminal-to-Exposed-Pad	K	0.20	-	-

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Package is saw singulated

3. Dimensioning and tolerancing per ASME Y14.5M

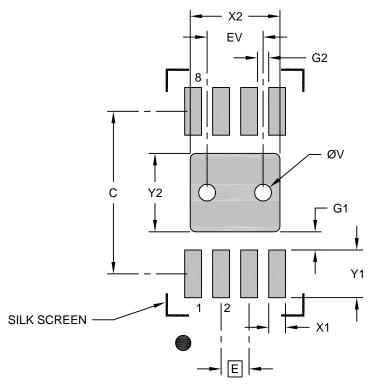
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-21355-Q4B Rev A Sheet 2 of 2

8-Lead Ultra Thin Plastic Dual Flat, No Lead Package (Q4B) - 2x3 mm Body [UDFN] Atmel Legacy YNZ Package

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	Units	Ν	IILLIMETER	S
Dimension	Limits	MIN	NOM	MAX
Contact Pitch	E		0.50 BSC	
Optional Center Pad Width	X2			1.60
Optional Center Pad Length	Y2			1.40
Contact Pad Spacing	С		2.90	
Contact Pad Width (X8)	X1			0.30
Contact Pad Length (X8)	Y1			0.85
Contact Pad to Center Pad (X8)	G1	0.20		
Contact Pad to Contact Pad (X6)	G2	0.33		
Thermal Via Diameter	V		0.30	
Thermal Via Pitch	EV		1.00	

Notes:

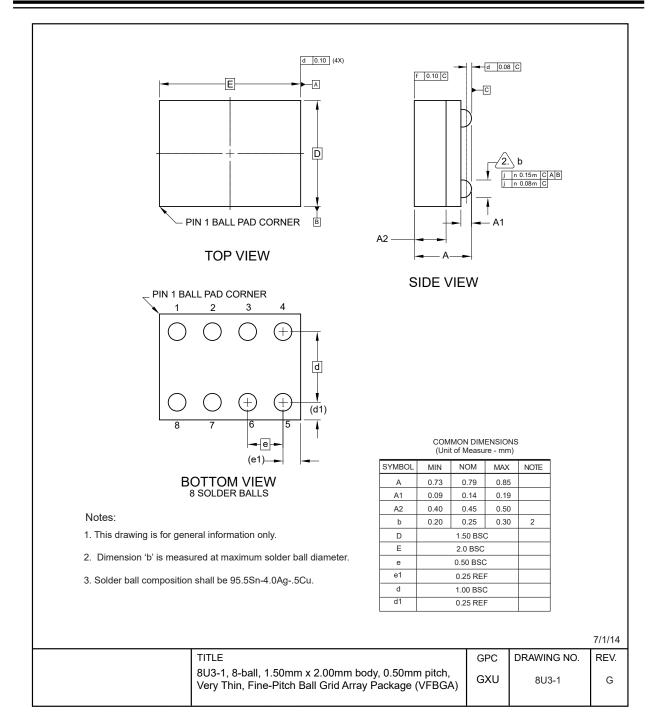
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

2. For best soldering results, thermal vias, if used, should be filled or tented to avoid solder loss during reflow process

Microchip Technology Drawing C04-21355-Q4B Rev A

Packaging Information



Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging.

10. Revision History

Revision A (October 2019)

Updated to Microchip template. Microchip DS20006251 replaces Atmel document 8707. Updated Part Marking Information. Added ESD rating. Removed the 8-pad XDFN detail and ordering code. Removed lead finish designation. Added POR recommendations section. Updated trace code format in package markings. Updated section content throughout for clarification. Updated the 8U3-1 VFBGA package drawing. Updated the SOIC, TSSOP and UDFN package drawings to the Microchip equivalents.

Atmel Document 8707 Revision F (January 2015)

Added the UDFN Expanded Quantity Option. Updated the 8MA2 package outline drawing and the ordering information section.

Atmel Document 8707 Revision E (May 2014)

Updated part markings, package drawings, package 8A2 to 8X, template, logos, and disclaimer page. No change to functional specification.

Atmel Document 8707 Revision D (April 2013)

Corrected WRSR waveform figure 4-5, bit 7 is not writable. Updated Atmel logos and disclaimer page.

Atmel Document 8707 Revision C (June 2011)

Corrected AT25040B-SSHL marking detail. Replaced 8A2 package drawing with version E.

Atmel Document 8707 Revision B (October 2010)

Removed Preliminary.

Atmel Document 8707 Revision B (March 2010)

Replaced 8Y6 with 8MA2.

Atmel Document 8707 Revision A (February 2010)

Initial document release.

The Microchip Website

Microchip provides online support via our website at http://www.microchip.com/. This website is used to make files and information easily available to customers. Some of the content available includes:

- **Product Support** Data sheets and errata, application notes and sample programs, design resources, user's guides and hardware support documents, latest software releases and archived software
- General Technical Support Frequently Asked Questions (FAQs), technical support requests, online discussion groups, Microchip design partner program member listing
- **Business of Microchip** Product selector and ordering guides, latest Microchip press releases, listing of seminars and events, listings of Microchip sales offices, distributors and factory representatives

Product Change Notification Service

Microchip's product change notification service helps keep customers current on Microchip products. Subscribers will receive email notification whenever there are changes, updates, revisions or errata related to a specified product family or development tool of interest.

To register, go to http://www.microchip.com/pcn and follow the registration instructions.

Customer Support

Users of Microchip products can receive assistance through several channels:

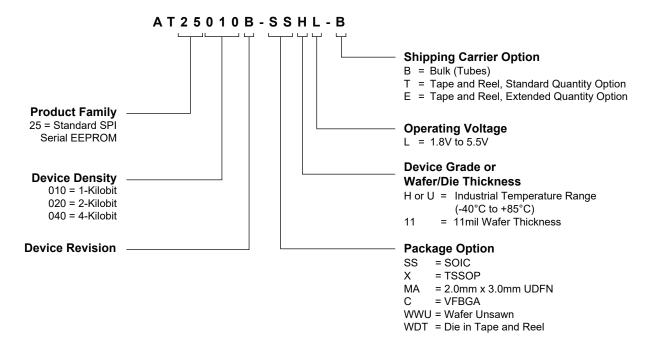
- Distributor or Representative
- · Local Sales Office
- Embedded Solutions Engineer (ESE)
- Technical Support

Customers should contact their distributor, representative or ESE for support. Local sales offices are also available to help customers. A listing of sales offices and locations is included in this document.

Technical support is available through the website at: http://www.microchip.com/support

Product Identification System

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.



Note: Refer to automotive data sheet for automotive grade ordering information.

Examples:

Device	Package	Package Drawing Code	Package Option	Shipping Carrier Option	Device Grade
AT25040B-SSHL-B	SOIC	SN	SS	Bulk (Tubes)	Industrial
AT25010B-SSHL-T	SOIC	SN	SS	Tape and Reel	Temperature (-40°C to 85°C)
AT25020B-SSHL-T	SOIC	SN	SS	Tape and Reel	, , , , , , , , , , , , , , , , , , ,
AT25020B-XHL-B	TSSOP	ST	Х	Bulk (Tubes)	
AT25010B-XHL-T	TSSOP	ST	Х	Tape and Reel	
AT25040B-MAHL-E	UDFN	Q4B	MA	Tape and Reel	
AT25020B-MAHL-T	UDFN	Q4B	MA	Tape and Reel	
AT25010B-MAHL-E	UDFN	Q4B	MA	Tape and Reel	
AT25040B-CUL-T	VFBGA	8U3-1	С	Tape and Reel	

Microchip Devices Code Protection Feature

Note the following details of the code protection feature on Microchip devices:

· Microchip products meet the specification contained in their particular Microchip Data Sheet.

- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- · Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Legal Notice

Information contained in this publication regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, MERCHANTABILITY OR FITNESS FOR PURPOSE. Microchip disclaims all liability arising from this information and its use. Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights unless otherwise stated.

Trademarks

The Microchip name and logo, the Microchip logo, Adaptec, AnyRate, AVR, AVR logo, AVR Freaks, BesTime, BitCloud, chipKIT, chipKIT logo, CryptoMemory, CryptoRF, dsPIC, FlashFlex, flexPWR, HELDO, IGLOO, JukeBlox, KeeLoq, Kleer, LANCheck, LinkMD, maXStylus, maXTouch, MediaLB, megaAVR, Microsemi, Microsemi logo, MOST, MOST logo, MPLAB, OptoLyzer, PackeTime, PIC, picoPower, PICSTART, PIC32 logo, PolarFire, Prochip Designer, QTouch, SAM-BA, SenGenuity, SpyNIC, SST, SST Logo, SuperFlash, Symmetricom, SyncServer, Tachyon, TempTrackr, TimeSource, tinyAVR, UNI/O, Vectron, and XMEGA are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

APT, ClockWorks, The Embedded Control Solutions Company, EtherSynch, FlashTec, Hyper Speed Control, HyperLight Load, IntelliMOS, Libero, motorBench, mTouch, Powermite 3, Precision Edge, ProASIC, ProASIC Plus, ProASIC Plus logo, Quiet-Wire, SmartFusion, SyncWorld, Temux, TimeCesium, TimeHub, TimePictra, TimeProvider, Vite, WinPath, and ZL are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Adjacent Key Suppression, AKS, Analog-for-the-Digital Age, Any Capacitor, AnyIn, AnyOut, BlueSky, BodyCom, CodeGuard, CryptoAuthentication, CryptoAutomotive, CryptoCompanion, CryptoController, dsPICDEM, dsPICDEM.net, Dynamic Average Matching, DAM, ECAN, EtherGREEN, In-Circuit Serial Programming, ICSP, INICnet, Inter-Chip Connectivity, JitterBlocker, KleerNet, KleerNet logo, memBrain, Mindi, MiWi, MPASM, MPF, MPLAB Certified logo, MPLIB, MPLINK, MultiTRAK, NetDetach, Omniscient Code Generation, PICDEM, PICDEM.net, PICkit, PICtail, PowerSmart, PureSilicon, QMatrix, REAL ICE, Ripple Blocker, SAM-ICE, Serial Quad I/O, SMART-I.S., SQI, SuperSwitcher, SuperSwitcher II, Total Endurance, TSHARC, USBCheck, VariSense, ViewSpan, WiperLock, Wireless DNA, and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

The Adaptec logo, Frequency on Demand, Silicon Storage Technology, and Symmcom are registered trademarks of Microchip Technology Inc. in other countries.

GestIC is a registered trademark of Microchip Technology Germany II GmbH & Co. KG, a subsidiary of Microchip Technology Inc., in other countries.

All other trademarks mentioned herein are property of their respective companies.

© 2019, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.

ISBN: 978-1-5224-5155-6

AMBA, Arm, Arm7, Arm7TDMI, Arm9, Arm11, Artisan, big.LITTLE, Cordio, CoreLink, CoreSight, Cortex, DesignStart, DynamIQ, Jazelle, Keil, Mali, Mbed, Mbed Enabled, NEON, POP, RealView, SecurCore, Socrates, Thumb, TrustZone, ULINK, ULINK2, ULINK-ME, ULINK-PLUS, ULINKpro, µVision, Versatile are trademarks or registered trademarks of Arm Limited (or its subsidiaries) in the US and/or elsewhere.

Quality Management System

For information regarding Microchip's Quality Management Systems, please visit http://www.microchip.com/quality.



Worldwide Sales and Service

MERICAS	ASIA/PACIFIC	ASIA/PACIFIC	EUROPE
Corporate Office	Australia - Sydney	India - Bangalore	Austria - Wels
355 West Chandler Blvd.	Tel: 61-2-9868-6733	Tel: 91-80-3090-4444	Tel: 43-7242-2244-39
Chandler, AZ 85224-6199	China - Beijing	India - New Delhi	Fax: 43-7242-2244-393
el: 480-792-7200	Tel: 86-10-8569-7000	Tel: 91-11-4160-8631	Denmark - Copenhagen
ax: 480-792-7277	China - Chengdu	India - Pune	Tel: 45-4450-2828
echnical Support:	Tel: 86-28-8665-5511	Tel: 91-20-4121-0141	Fax: 45-4485-2829
ttp://www.microchip.com/support	China - Chongging	Japan - Osaka	Finland - Espoo
Veb Address:	Tel: 86-23-8980-9588	Tel: 81-6-6152-7160	Tel: 358-9-4520-820
ttp://www.microchip.com	China - Dongguan	Japan - Tokyo	France - Paris
tlanta	Tel: 86-769-8702-9880	Tel: 81-3-6880- 3770	Tel: 33-1-69-53-63-20
uluth, GA	China - Guangzhou	Korea - Daegu	Fax: 33-1-69-30-90-79
el: 678-957-9614	Tel: 86-20-8755-8029	Tel: 82-53-744-4301	Germany - Garching
ax: 678-957-1455	China - Hangzhou	Korea - Seoul	Tel: 49-8931-9700
ustin, TX	Tel: 86-571-8792-8115	Tel: 82-2-554-7200	Germany - Haan
el: 512-257-3370	China - Hong Kong SAR	Malaysia - Kuala Lumpur	Tel: 49-2129-3766400
Boston	Tel: 852-2943-5100	Tel: 60-3-7651-7906	Germany - Heilbronn
/estborough, MA	China - Nanjing	Malaysia - Penang	Tel: 49-7131-72400
el: 774-760-0087	Tel: 86-25-8473-2460	Tel: 60-4-227-8870	Germany - Karlsruhe
ax: 774-760-0088	China - Qingdao	Philippines - Manila	Tel: 49-721-625370
chicago	Tel: 86-532-8502-7355	Tel: 63-2-634-9065	Germany - Munich
asca, IL	China - Shanghai	Singapore	Tel: 49-89-627-144-0
el: 630-285-0071	Tel: 86-21-3326-8000	Tel: 65-6334-8870	Fax: 49-89-627-144-44
ax: 630-285-0075	China - Shenyang	Taiwan - Hsin Chu	Germany - Rosenheim
allas	Tel: 86-24-2334-2829	Tel: 886-3-577-8366	Tel: 49-8031-354-560
ddison, TX	China - Shenzhen	Taiwan - Kaohsiung	Israel - Ra'anana
el: 972-818-7423	Tel: 86-755-8864-2200	Tel: 886-7-213-7830	Tel: 972-9-744-7705
ax: 972-818-2924	China - Suzhou	Taiwan - Taipei	Italy - Milan
etroit	Tel: 86-186-6233-1526	Tel: 886-2-2508-8600	Tel: 39-0331-742611
ovi, MI	China - Wuhan	Thailand - Bangkok	Fax: 39-0331-466781
el: 248-848-4000	Tel: 86-27-5980-5300	Tel: 66-2-694-1351	Italy - Padova
ouston, TX	China - Xian	Vietnam - Ho Chi Minh	Tel: 39-049-7625286
el: 281-894-5983	Tel: 86-29-8833-7252	Tel: 84-28-5448-2100	Netherlands - Drunen
dianapolis	China - Xiamen		Tel: 31-416-690399
oblesville, IN	Tel: 86-592-2388138		Fax: 31-416-690340
el: 317-773-8323	China - Zhuhai		Norway - Trondheim
ax: 317-773-5453	Tel: 86-756-3210040		Tel: 47-72884388
el: 317-536-2380			Poland - Warsaw
os Angeles			Tel: 48-22-3325737
lission Viejo, CA			Romania - Bucharest
el: 949-462-9523			Tel: 40-21-407-87-50
ax: 949-462-9608			Spain - Madrid
el: 951-273-7800			Tel: 34-91-708-08-90
aleigh, NC			Fax: 34-91-708-08-91
el: 919-844-7510			Sweden - Gothenberg
ew York, NY			Tel: 46-31-704-60-40
el: 631-435-6000			Sweden - Stockholm
an Jose, CA			Tel: 46-8-5090-4654
el: 408-735-9110			UK - Wokingham
el: 408-436-4270			Tel: 44-118-921-5800
anada - Toronto			Fax: 44-118-921-5820
el: 905-695-1980			1 ax. ++-110-321-3020
ax: 905-695-2078			

单击下面可查看定价,库存,交付和生命周期等信息

>>Microchip Technology